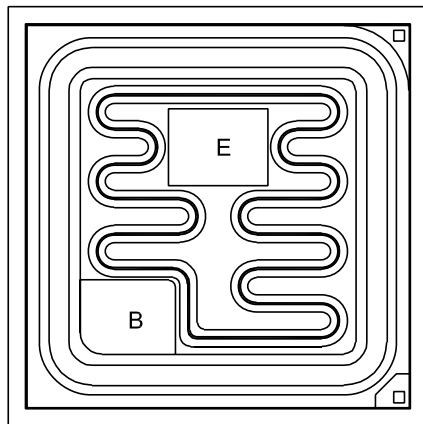


**PROCESS DETAILS**

Process	EPITAXIAL PLANAR
Die Size	19 x 19 MILS
Die Thickness	7.1 MILS
Base Bonding Pad Area	3.5 x 4.3 MILS
Emitter Bonding Pad Area	3.5 x 4.5 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au - 18,000Å

**GEOMETRY**

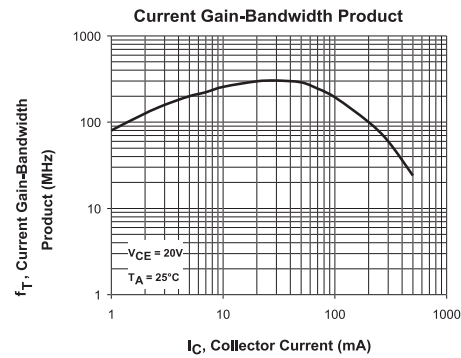
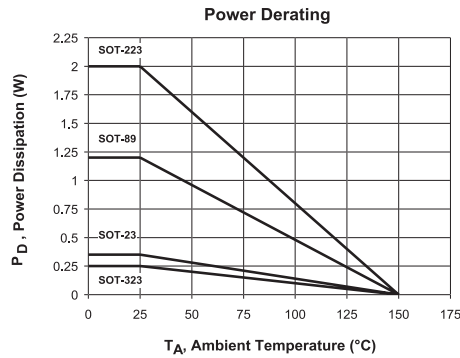
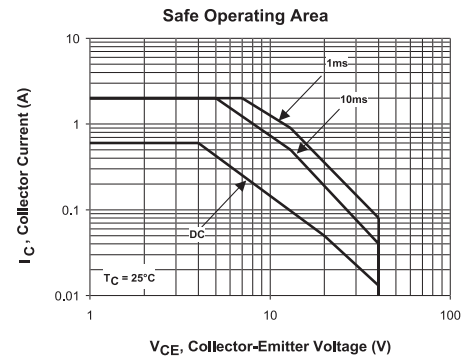
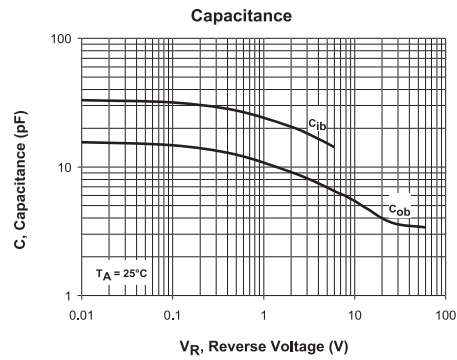
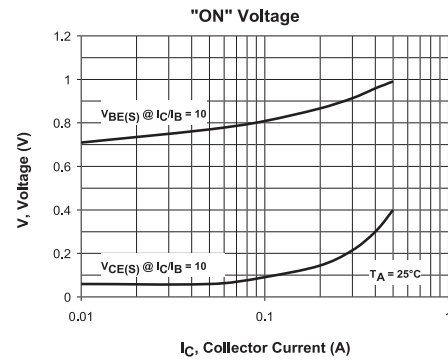
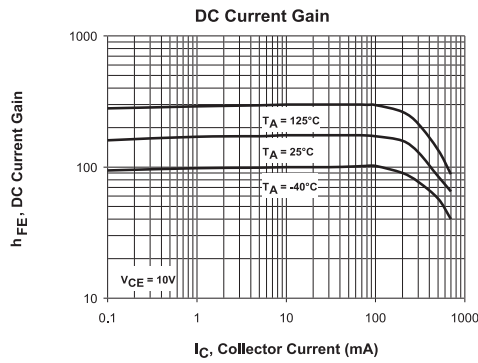


**GROSS DIE PER 4 INCH WAFER**

30,600

**PRINCIPAL DEVICE TYPES**

2N2905A  
2N2907A  
CMPT2907A  
CMST2907A  
CXT2907A  
CZT2907A  
PN2907A



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R0 (31-May 2006)